

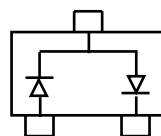
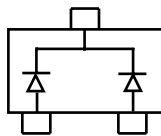
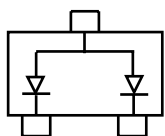
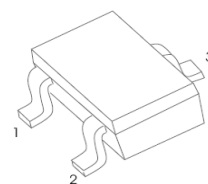


Plastic-Encapsulate Diodes

SWITCHING DIODE

SOT-523**FEATURES**

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance



BAW56T Marking: A1

BAV70T

Marking: A4

BAV99T

Marking: A7

Maximum Ratings @Ta=25°C

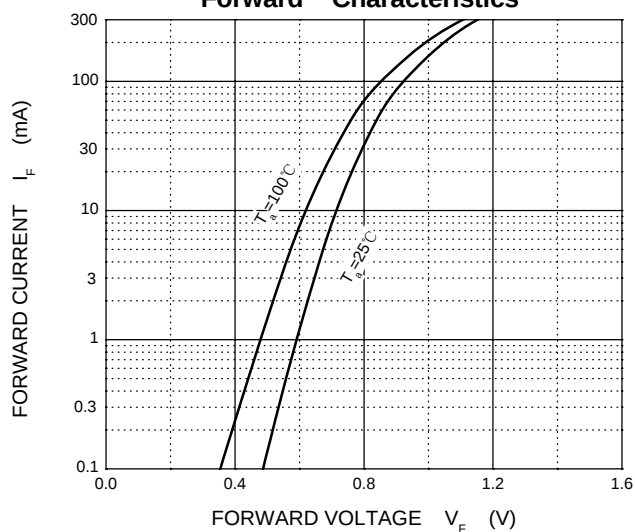
Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	85	V
Forward current	I_o	75	mA
Forward power dissipation	P_D	150	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

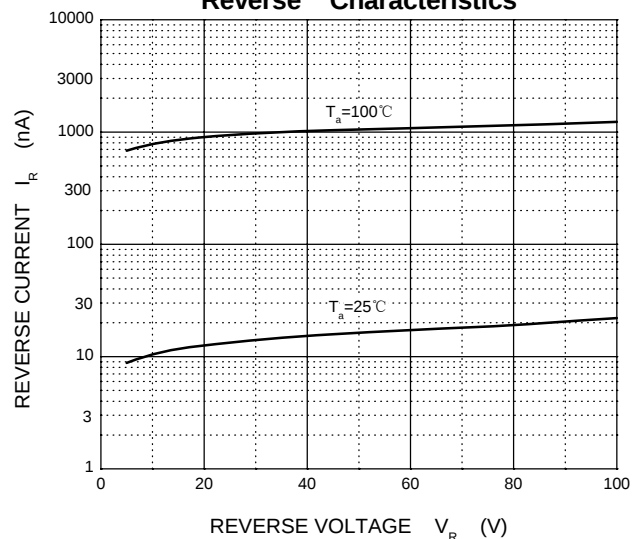
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=1\mu A$	85		V
Reverse voltage leakage current	I_{R1}	$V_R=75V$		2	μA
	I_{R2}	$V_R=25V$		0.03	μA
Forward voltage	V_F	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$		715 855 1000 1250	mV
Diode capacitance	C_D	$V_R=0$ $f=1MHz$		1.5	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1\times I_R, R_L=100\Omega$		4	ns



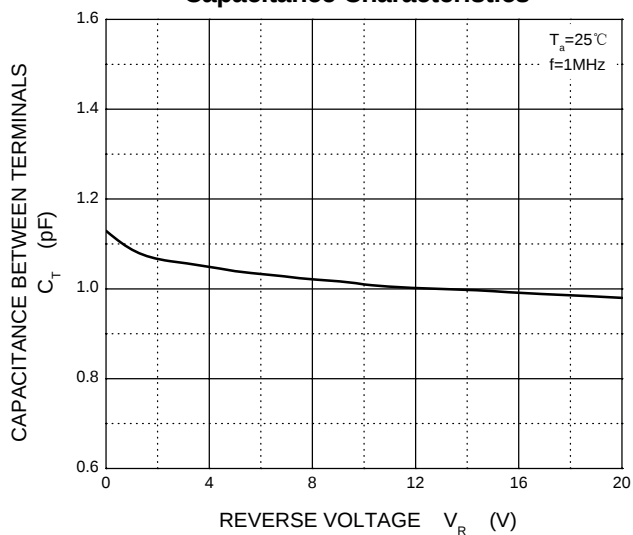
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

